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ABSTRACT

DUAL-HYBRID LINER FORMATION WITHOUT EXPOSING SILICIDE LAYER TO PHOTORESIST STRIPPING CHEMICALS

Methods of fabricating a semiconductor device including a dual-hybrid liner in which an underlying silicide layer (68) is protected from photoresist stripping chemicals by using a hard mask (110) as a pattern during etching, rather than using a photoresist. The hard mask (110) prevents exposure of a silicide layer (68) to photoresist stripping chemicals and provides very good lateral dimension control such that the two nitride liners are well aligned.

Fig. 9.



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